

# FDD8770/FDU8770 N-Channel PowerTrench® MOSFET

25V, 35A, 4.0mΩ



## General Description

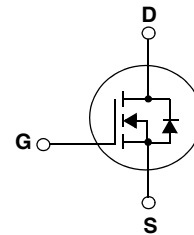
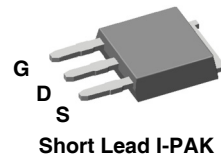
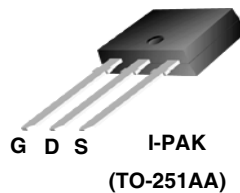
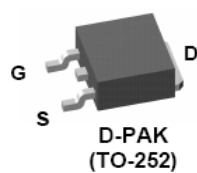
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$  and fast switching speed.

## Features

- Max  $r_{DS(on)}$  = 4.0mΩ at  $V_{GS} = 10V$ ,  $I_D = 35A$
- Max  $r_{DS(on)}$  = 5.5mΩ at  $V_{GS} = 4.5V$ ,  $I_D = 35A$
- Low gate charge:  $Q_{g(10)} = 52nC(Typ)$ ,  $V_{GS} = 10V$
- Low gate resistance
- RoHS Compliant

## Application

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture



## MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package Limited)	35	A
	-Continuous (Die Limited)	210	
	-Pulsed (Note 1)	407	
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	113	mJ
$P_D$	Power Dissipation	115	W
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to 175	$^\circ C$

## Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case TO-252, TO-251	1.3	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, TO-251	100	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	52	$^\circ C/W$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8770	FDD8770	TO-252AA	13"	12mm	2500 units
FDU8770	FDU8770	TO-251AA	N/A(Tube)	N/A	75 units
FDU8770	FDU8770_F071	TO-251AA	N/A(Tube)	N/A	75 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	25			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		13.6		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$			1 250	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.2	1.6	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-5.9		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 35\text{A}$		3.3	4.0	m $\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 35\text{A}$		4.0	5.5	
		$V_{GS} = 10\text{V}, I_D = 35\text{A}$ $T_J = 175^\circ\text{C}$		4.8	5.9	

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 13\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		2795	3720	pF
$C_{oss}$	Output Capacitance			685	915	pF
$C_{rss}$	Reverse Transfer Capacitance			450	675	pF
$R_g$	Gate Resistance		$f = 1\text{MHz}$	1.5		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 13\text{V}, I_D = 35\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 5\Omega$		10	20	ns
$t_r$	Rise Time			12	22	ns
$t_{d(off)}$	Turn-Off Delay Time			49	78	ns
$t_f$	Fall Time			25	40	ns
$Q_g$	Total Gate Charge		$V_{GS} = 0\text{V to } 10\text{V}$		52	73
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{V to } 5\text{V}$	$V_{DD} = 13\text{V}$ $I_D = 35\text{A}$ $I_g = 1.0\text{mA}$	29	41	nC
$Q_{gs}$	Gate to Source Gate Charge			8.1		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			11		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 35\text{A}$		0.84	1.25	V
		$V_{GS} = 0\text{V}, I_S = 15\text{A}$		0.79	1.0	
$t_{rr}$	Reverse Recovery Time	$I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$		32	48	ns
$Q_{rr}$	Reverse Recovery Charge	$I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$		25	38	nC

**Notes:**

- 1: Pulse time < 300 $\mu\text{s}$ , Duty cycle = 2%.
- 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.3\text{mH}$ ,  $I_{AS} = 27.5\text{A}$ ,  $V_{DD} = 23\text{V}$ ,  $V_{GS} = 10\text{V}$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

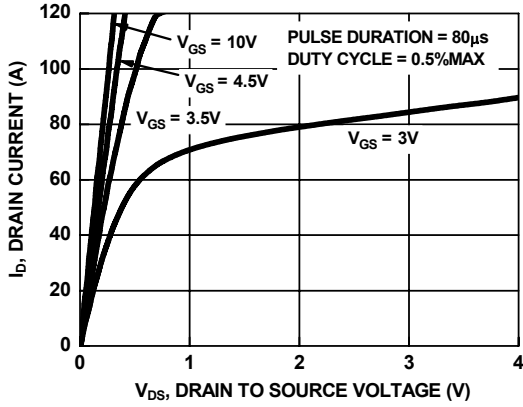


Figure 1. On Region Characteristics

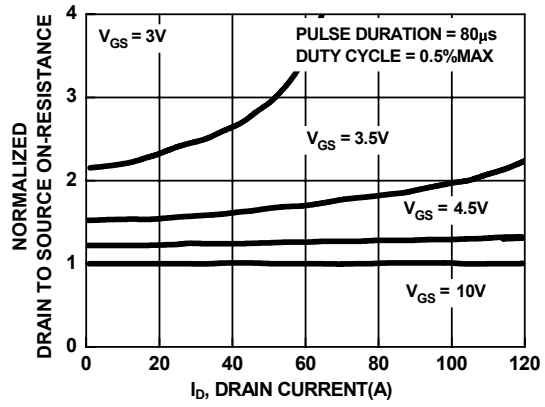


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

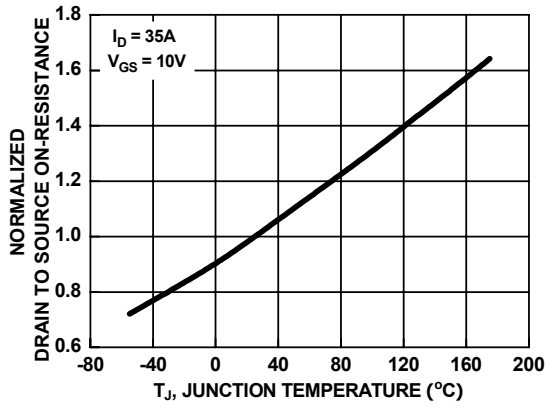


Figure 3. Normalized On Resistance vs Junction Temperature

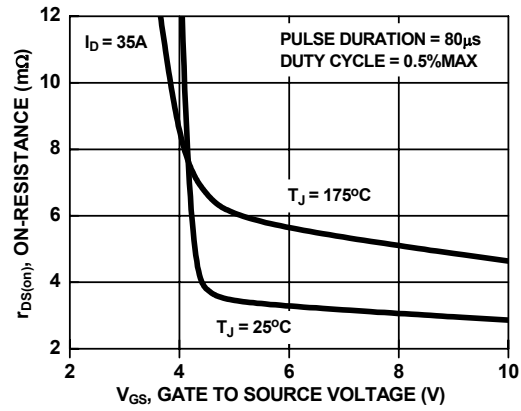


Figure 4. On-Resistance vs Gate to Source Voltage

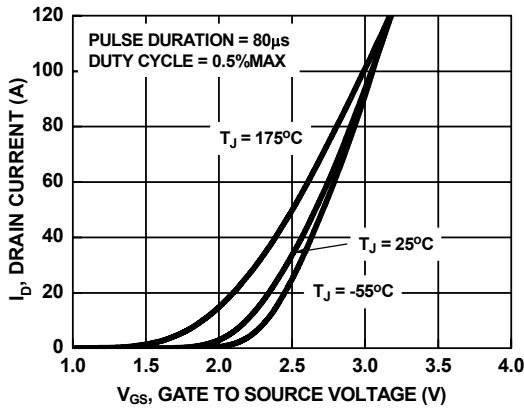


Figure 5. Transfer Characteristics

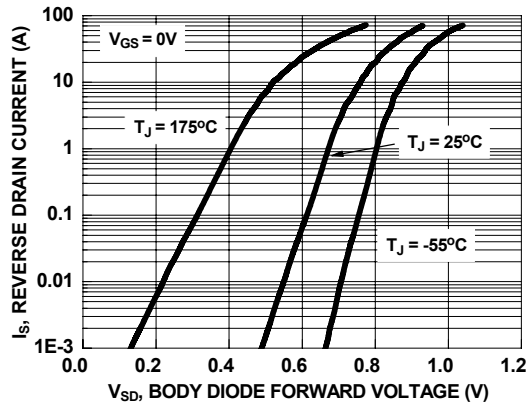


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

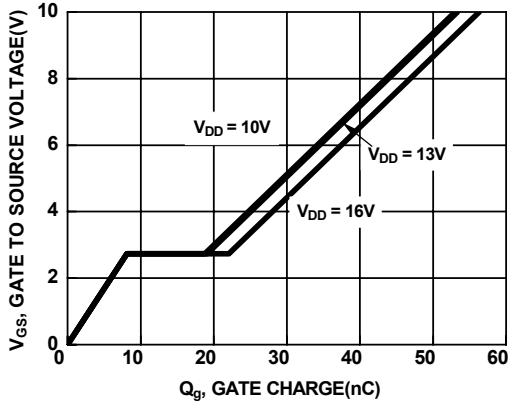


Figure 7. Gate Charge Characteristics

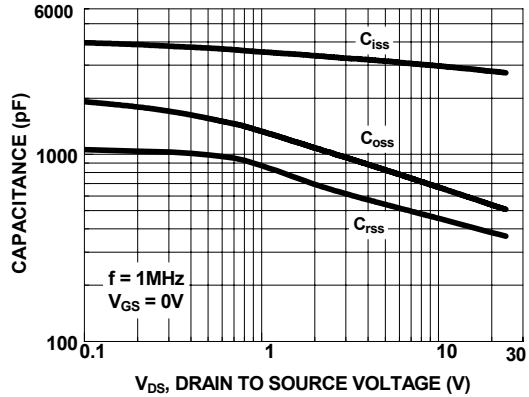


Figure 8. Capacitance vs Drain to Source Voltage

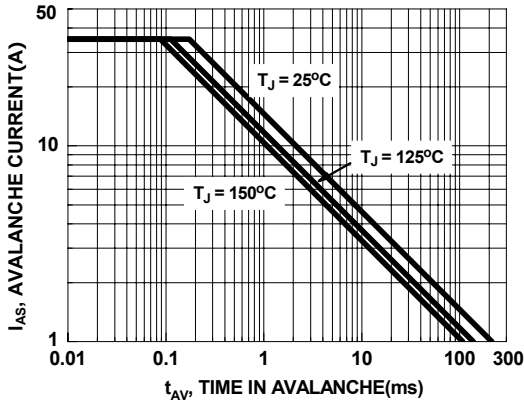


Figure 9. Unclamped Inductive Switching Capability

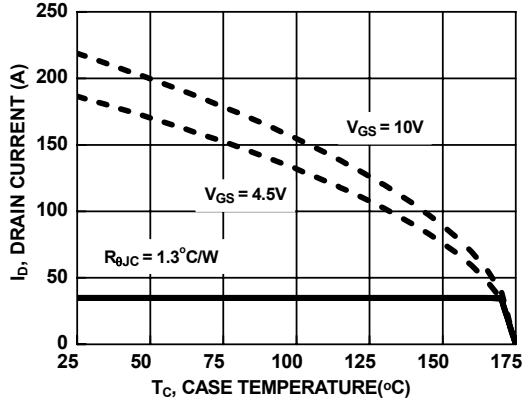


Figure 10. Maximum Continuous Drain Current vs Case Temperature

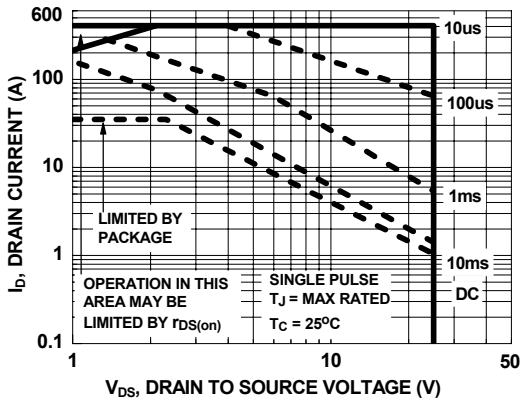


Figure 11. Forward Bias Safe Operating Area

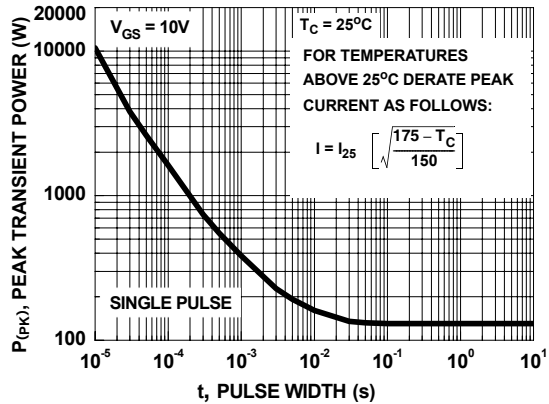
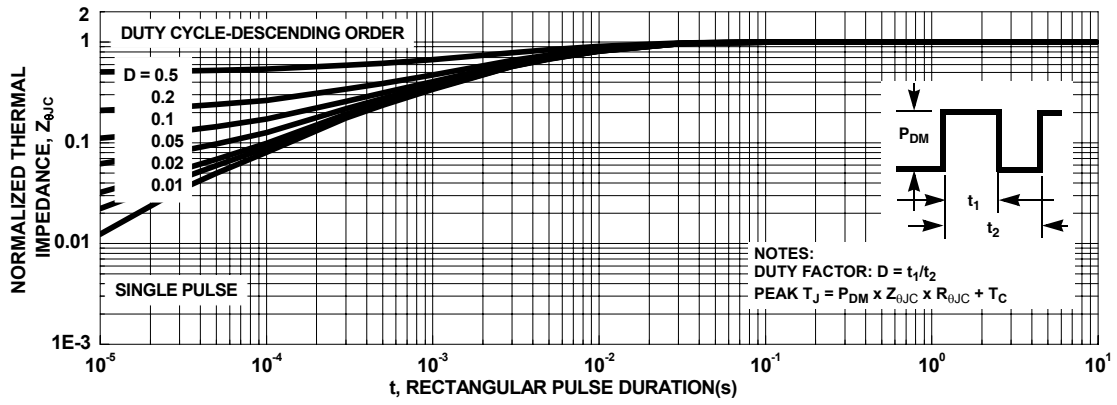


Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



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